

R07DS1321EJ0100

Rev.1.00

Jan 25, 2016

μ**PA2738GR**

P-channel MOSFET

–30 V, –10 A, 15 mΩ

Description

The μ PA2738GR is P-channel MOS Field Effect Transistor designed for DC/DC converter and power management applications of portable equipment.

Features

- $V_{DSS} = -30 V (T_A = 25^{\circ}C)$
- Low on-state resistance
 - ---- $R_{DS(on)} = 15 \text{ m}\Omega \text{ MAX.} (V_{GS} = -10 \text{ V}, I_D = -10 \text{ A})$
- 4.5 V Gate-drive available
- Small and surface mount package (SOP-8)
- Pb-free and Halogen free

Ordering Information



SOP-8

Part No.	LEAD PLATING	PACKING	Package
μ PA2738GR-E1-AX	Ni / Pd / Au	Tape 2500 p/reel	SOP-8
μ PA2738GR-E2-AX	NI/Fu/Au	Tape 2000 p/Teel	0.085 g TYP.

Absolute Maximum Ratings $(T_A = 25^{\circ}C)$

Item	Symbol	Ratings	Unit	
Drain to Source Voltage ($V_{GS} = 0 V$)	V _{DSS}	-30	V	
Gate to Source Voltage ($V_{DS} = 0 V$)	V _{GSS}	∓20	V	
Drain Current (DC)	I _{D(DC)}	∓10	A	
Drain Current (pulse) *1	I _{D(pulse)}	∓100	A	
Total Power Dissipation *2	P _{T1}	1.1	W	
Total Power Dissipation (PW = 10 sec) *2	P _{T2}	2.5	W	
Channel Temperature	T _{ch}	150	°C	
Storage Temperature	T _{stg}	-55 to +150	°C	
Single Avalanche Current *3	I _{AS}	10	A	
Single Avalanche Energy *3	E _{AS}	10	mJ	

Thermal Resistance

Channel to Ambient Thermal Resistance *2 Rth(ch-A) 114 °C/W

Notes: *1. PW \leq 10 μ s, Duty Cycle \leq 1%

- *2. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mmt
- *3. Starting T_{ch} = 25°C, V_{DD} = -15 V, R_G = 25 Ω , V_{GS} = -20 \rightarrow 0 V, L = 100 μ H

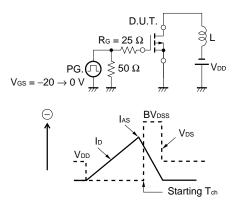


Electrical Characteristics (T_A = 25°C)

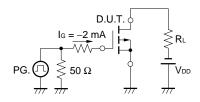
ltem	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			-1	μA	$V_{DS} = -30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$
Gate Leakage Current	I _{GSS}			∓100	nA	$V_{GS} = \mp 20 \text{ V}, V_{DS} = 0 \text{ V}$
Gate Cut-off Voltage	V _{GS(off)}	-1.0		-2.5	V	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ mA}$
Forward Transfer Admittance *1	y _{fs}	4			S	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -5.0 \text{ A}$
Drain to Source On-state	R _{DS(on)1}		12	15	mΩ	$V_{GS} = -10 \text{ V}, I_D = -10 \text{ A}$
Resistance *1	R _{DS(on)2}		19	29	mΩ	$V_{GS} = -4.5 \text{ V}, I_D = -10 \text{ A}$
Input Capacitance	C _{iss}		1450		pF	$V_{DS} = -10 V$,
Output Capacitance	Coss		710		pF	$V_{GS} = 0 V,$
Reverse Transfer Capacitance	C _{rss}		650		pF	f = 1 MHz
Turn-on Delay Time	t _{d(on)}		14		ns	$V_{DD} = -15 \text{ V}, I_D = -5.0 \text{ A},$
Rise Time	t _r		30		ns	$V_{GS} = -10 V,$
Turn-off Delay Time	t _{d(off)}		60		ns	$R_G = 10 \Omega$
Fall Time	t _f		50		ns	
Total Gate Charge	Q _G		37		nC	$V_{DD} = -24 V,$
Gate to Source Charge	Q _{GS}		2.5		nC	$V_{GS} = -10 V$,
Gate to Drain Charge	Q _{GD}		20		nC	$I_{\rm D} = -10 \ {\rm A}$
Body Diode Forward Voltage *1	V _{F(S-D)}		0.86		V	$I_F = 10 \text{ A}, V_{GS} = 0 \text{ V}$
Reverse Recovery Time	t _{rr}		47		ns	$I_F = 10 \text{ A}, V_{GS} = 0 \text{ V},$
Reverse Recovery Charge	Q _{rr}		43		nC	di/dt = 100 A/µs

Note: *1. Pulsed

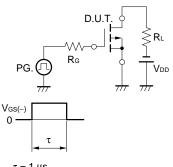
TEST CIRCUIT 1 AVALANCHE CAPABILITY



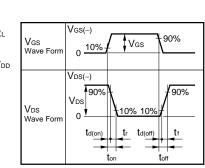
TEST CIRCUIT 3 GATE CHARGE



TEST CIRCUIT 2 SWITCHING TIME





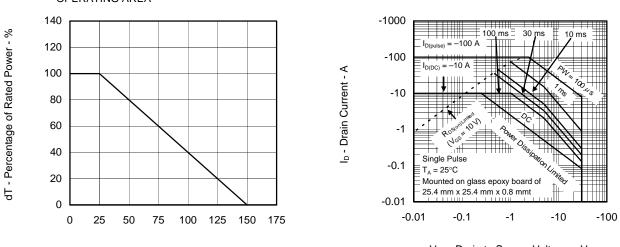




TYPICAL CHARACTERISTICS ($T_A = 25^{\circ}C$)

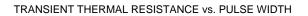
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

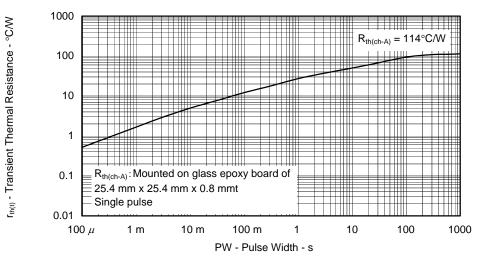
FORWARD BIAS SAFE OPERATING AREA



 T_A - Ambient Temperature - °C

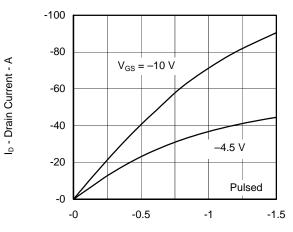
V_{DS} - Drain to Source Voltage - V



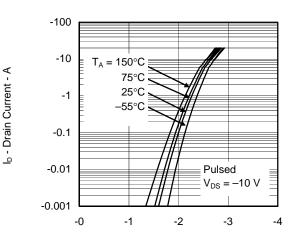




FORWARD TRANSFER CHARACTERISTICS

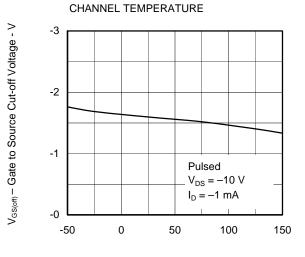


 V_{DS} - Drain to Source Voltage - V



V_{GS} - Gate to Source Voltage - V

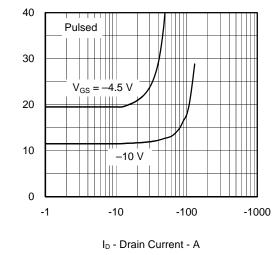


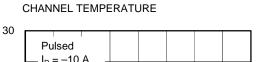


GATE TO SOURCE CUT-OFF VOLTAGE vs.

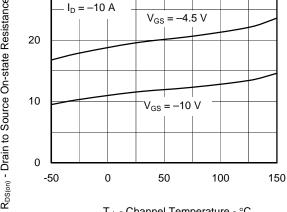


DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



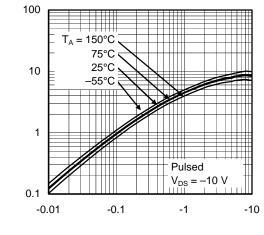


DRAIN TO SOURCE ON-STATE RESISTANCE vs.



T_{ch} - Channel Temperature - °C

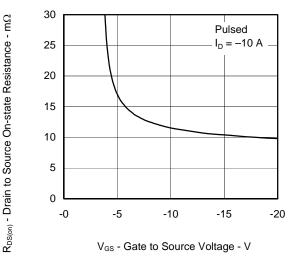
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



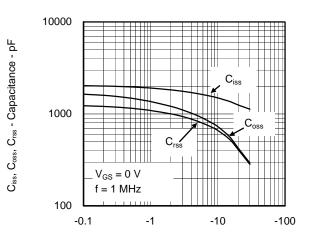
 $\mid y_{fs} \mid$ - Forward Transfer Admittance - S

I_D - Drain Current - A

DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



V_{DS} - Drain to Source Voltage - V

 $R_{\text{DS(on)}}$ - Drain to Source On-state Resistance - $m\Omega$



-25 -10 V_{DD}=-24 V V_{DS} - Drain to Source Voltage - V 12 V_ -20 -8 V 6 V_{DS} V_{GS} -15 -6 -10 -4 -5 -2 $I_{\rm D} = -10 \ {\rm A}$ -0 -0 10 20 30 0 40

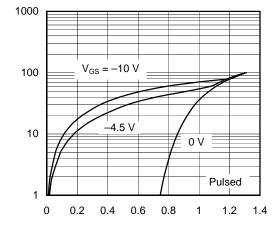
V_{GS} - Gate to Source Voltage - V

IF - Diode Forward Current - A

DYNAMIC INPUT/OUTPUT CHARACTERISTICS

Q_G - Gate Charge - nC

SOURCE TO DRAIN DIODE FORWARD VOLTAGE

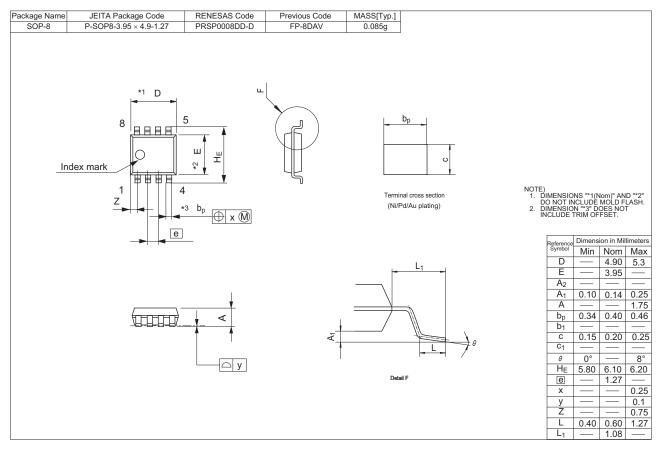


 $V_{\text{F(S-D)}}$ - Source to Drain Voltage - V

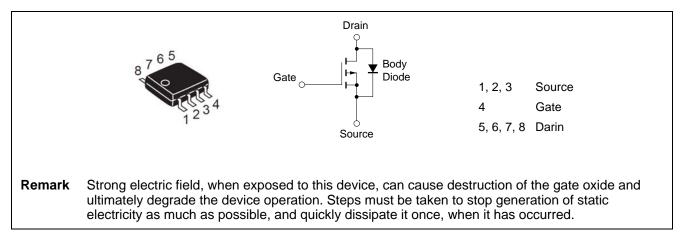


Package Drawings (Unit: mm)

SOP-8



Equivalent Circuit





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